
2SK1401, 2SK1401A

Silicon N-Channel MOS FET

HITACHI

Application

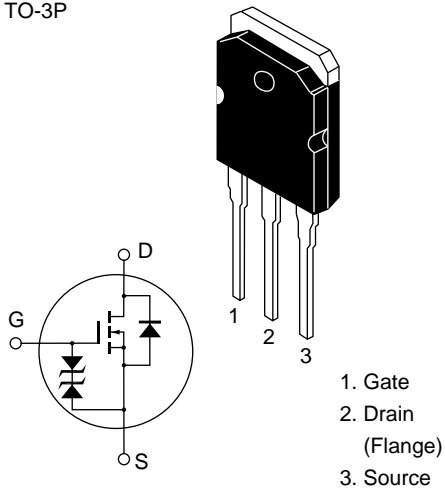
High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline

TO-3P



2SK1401, 2SK1401A

Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Ratings	Unit
Drain to source voltage	2SK1401	V_{DSS}	300	V
	2SK1401A		350	
Gate to source voltage		V_{GSS}	±30	V
Drain current		I_D	15	A
Drain peak current		$I_{D(pulse)}^{*1}$	60	A
Body to drain diode reverse drain current		I_{DR}	15	A
Channel dissipation		Pch^{*2}	100	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55 to +150	°C

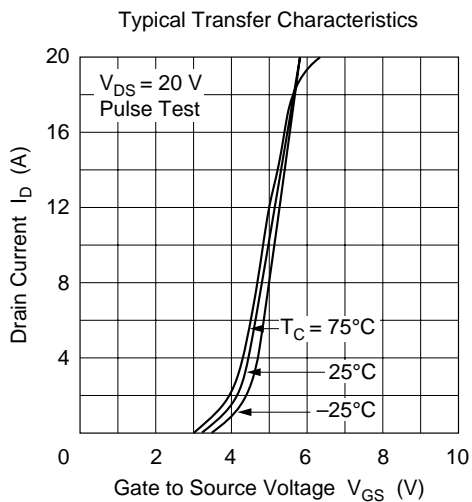
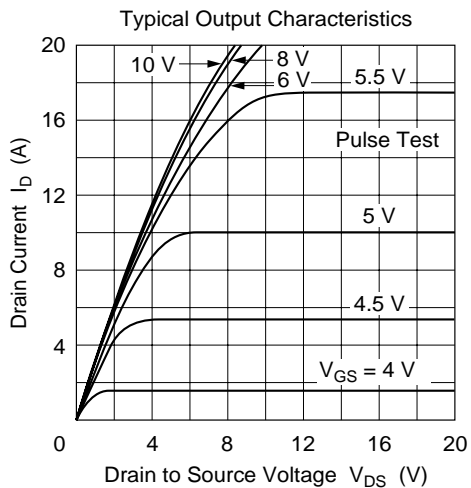
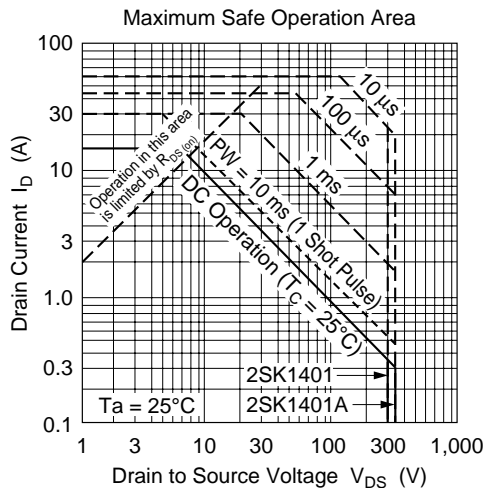
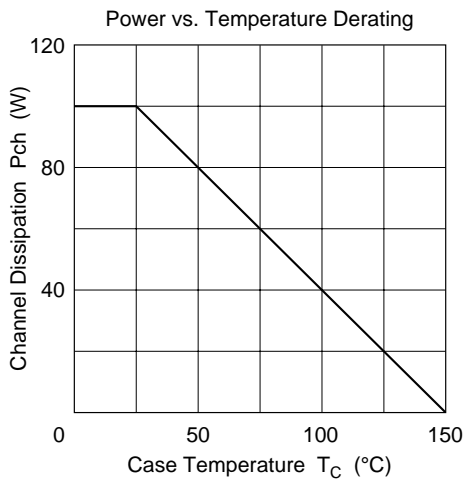
Notes: 1. PW 10 μs, duty cycle 1%

2. Value at T_c = 25°C

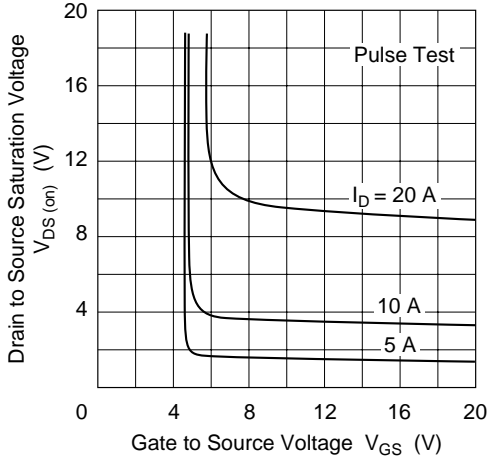
Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	K1401 K1401A	$V_{(BR)DSS}$	300	—	—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage		$V_{(BR)GSS}$	±30	—	—	V	$I_G = \pm 100 \text{ } \mu\text{A}, V_{DS} = 0$
Gate to source leak current		I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	K1401 K1401A	I_{DSS}	—	—	250	μA	$V_{DS} = 240 \text{ V}, V_{GS} = 0$ $V_{DS} = 280 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage		$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	K1401 K1401A	$R_{DS(on)}$	—	0.25 0.30	0.35 0.40		$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance		yfs	6	9.5	—	S	$I_D = 8 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance		Ciss	—	1250	—	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance		Coss	—	420	—	pF	$f = 1 \text{ MHz}$
Reverse transfer capacitance		Crss	—	70	—	pF	
Turn-on delay time		$t_{d(on)}$	—	15	—	ns	$I_D = 8 \text{ A}, V_{GS} = 10 \text{ V},$
Rise time		t_r	—	80	—	ns	$R_L = 3.75$
Turn-off delay time		$t_{d(off)}$	—	100	—	ns	
Fall time		t_f	—	55	—	ns	
Body to drain diode forward voltage		V_{DF}	—	1.05	—	V	$I_F = 15 \text{ A}, V_{GS} = 0$
Body to drain diode reverse recovery time		t_{rr}	—	370	—	ns	$I_F = 15 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

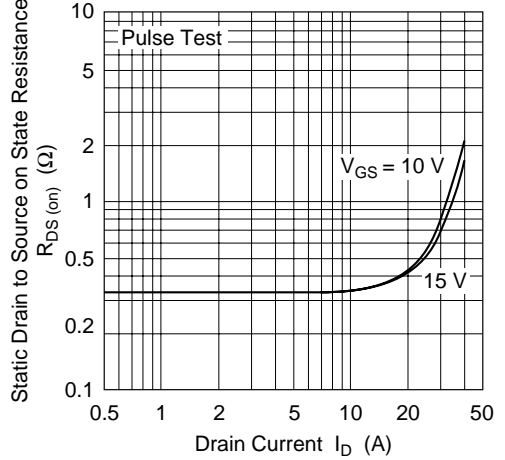
Note: 1. Pulse test



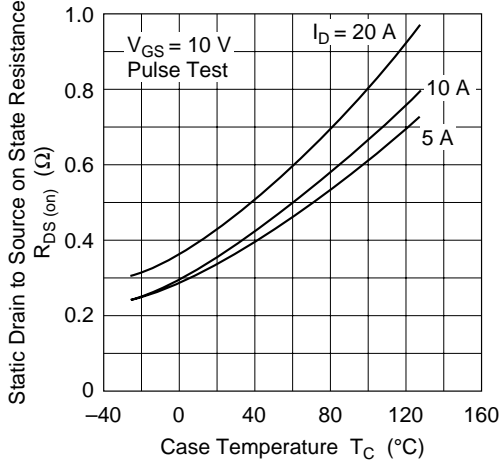
Drain to Source Saturation Voltage vs. Gate to Source Voltage



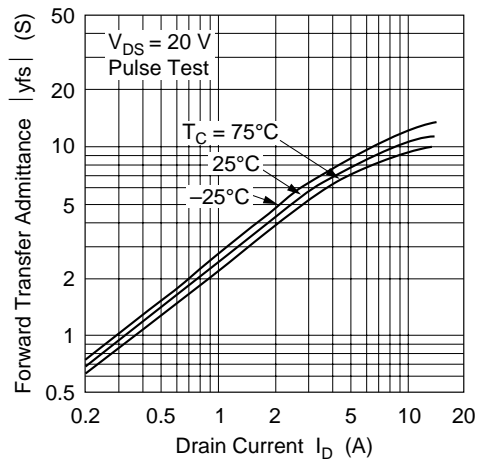
Static Drain to Source on State Resistance vs. Drain Current



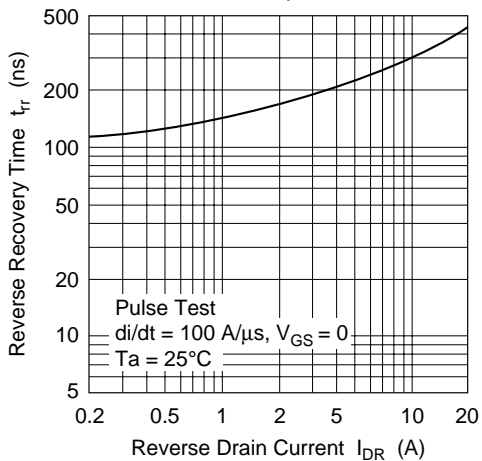
Static Drain to Source on State Resistance vs. Temperature



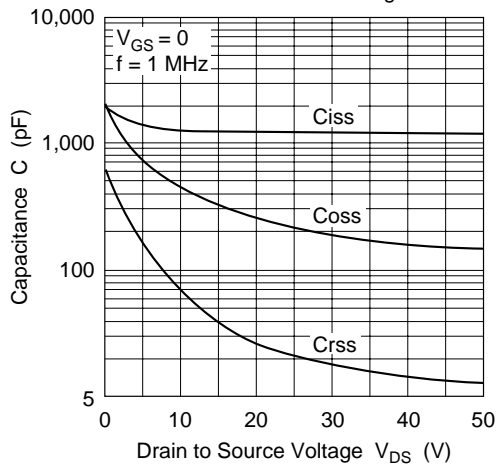
Forward Transfer Admittance vs. Drain Current



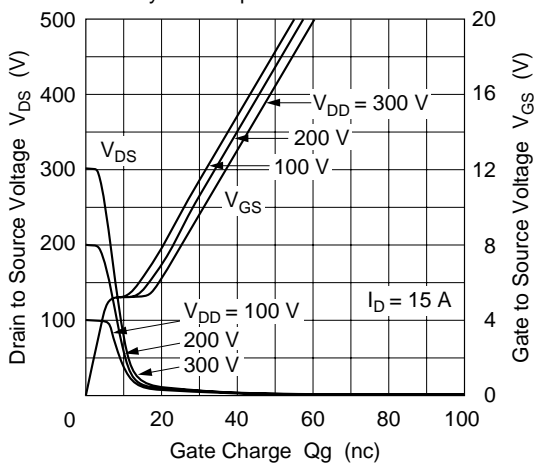
Body to Drain Diode Reverse Recovery Time



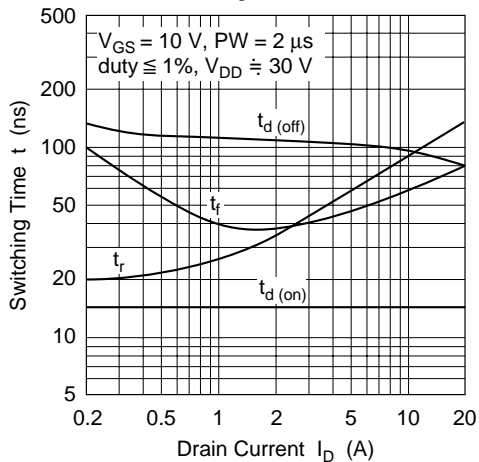
Typical Capacitance vs. Drain to Source Voltage

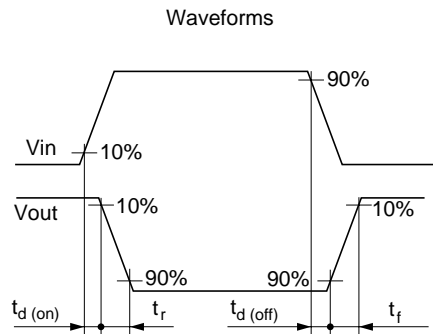
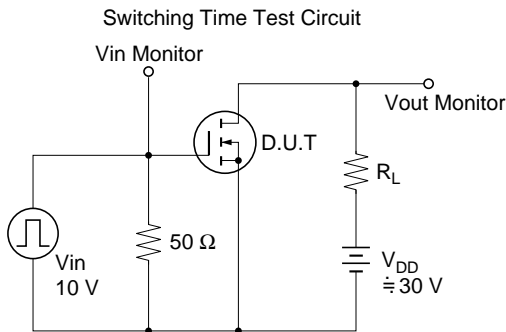
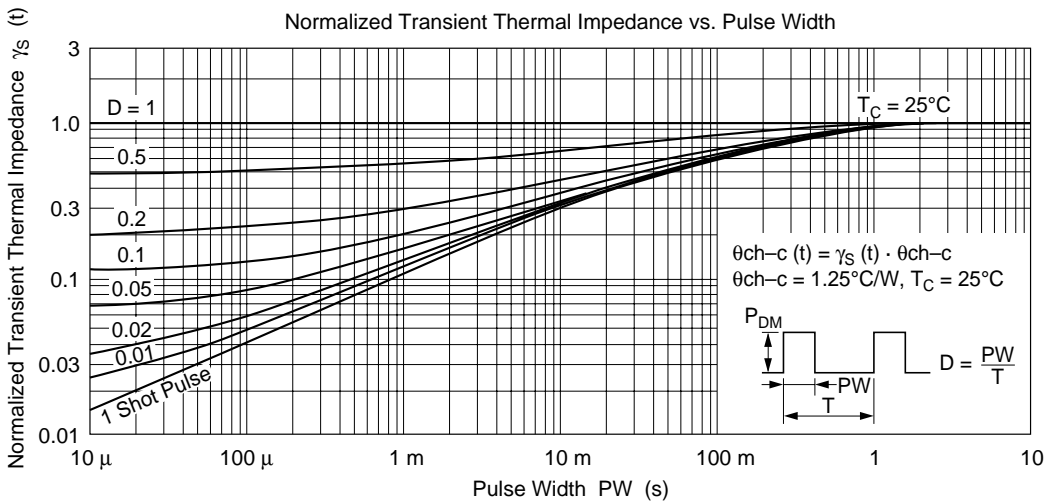
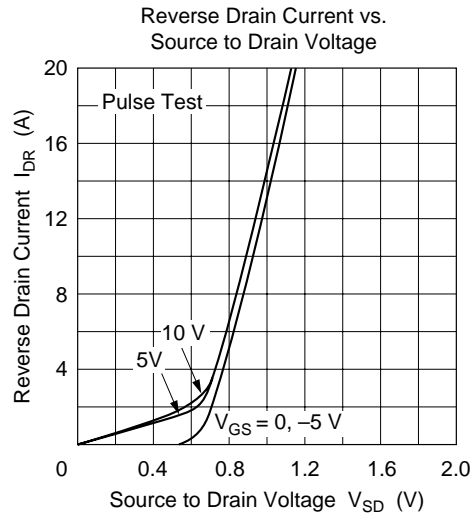


Dynamic Input Characteristics



Switching Characteristics





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